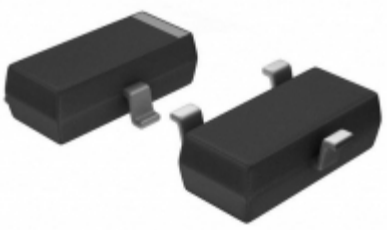










	<p>SI2377EDS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2377EDS-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET P-CH 20V 4.4A SOT-23</p>
	<p>Datenblätter:  SI2377EDS-T1-GE3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, 86254 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
<p>Image may be representation. See specs for product details.</p>	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

Spezifikationen

Teilenummer	SI2377EDS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 4.4A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	86254 pcs Stock
detaillierte Beschreibung	P-Channel 20V 4.4A (Tc) 1.25W (Ta), 1.8W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1.25W (Ta), 1.8W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.4A (Tc)
Rds On (Max) @ Id, Vgs	61 mOhm @ 3.2A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	21nC @ 8V
Antriebsspannung (Max Rds On, Min Rds On)	1.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2377EDS-T1-GE3TR

SI2377EDS-T1-GE3 ist neu im Original, Suche SI2377EDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2377EDS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2377EDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2392ADS-T1-GE3 Vishay / Siliconix MOSFET N-CH 100V 3.1A SOT-23</p>	 <p>SI2377EDS-T1-E3 VISHAY SI2377EDS-T1-E3 VISHAY</p>	 <p>SI2392ADS-T1-E3 VISHAY SI2392ADS-T1-E3 VISHAY</p>	 <p>SI2377DS-T1-GE3 V SI2377DS-T1-GE3 V</p>
 <p>SI2392ADS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 3.1A SOT-23</p>	 <p>SI2392DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 100V 3.1A SOT-23</p>	 <p>SI2392DS-T1-E3 AOS SI2392DS-T1-E3 AOS</p>	 <p>SI2377EDS-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 4.4A SOT-23</p>

heiße Teile

Mehr

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|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊛ SI2351DS-T1-GE3 | ↔ SI2356DS-T1-GE3 | ⇒ SI2356DS-T1-GE3 | D SI2365EDS | ⇒ SI2365EDS-T1-GE3 |
| ⊣ SI2365EDS-T1-GE3 | ⊛ SI2366DS-T1-E3 | D SI2366DS-T1-GE | ⇒ SI2366DS-T1-GE3 | ⇒ SI2366DS-T1-GE3 |
| ⊛ SI2367DS-T1-E3 | ⊣ SI2367DS-T1-GE3 | ⊛ SI2367DS-T1-GE3 | ↔ SI2369DS-T1-GE3 | ⇒ SI2369DS-T1-GE3 |
| D SI2371EDS-T1-GE3 | ⊛ SI2371EDS-T1-GE3 | ⊣ SI2372DS-T1-E3 | ⊛ SI2372DS-T1-GE3 | ⇒ SI2372DS-T1-GE3 |
| ⇒ SI2374DS-T1-GE3 | ↔ SI2374DS-T1-GE3 | ⊛ SI2377DS-T1-GE3 | ⊣ SI2377EDS | ⇒ SI2377EDS-T1-E3 |
| ↔ SI2377EDS-T1-GE3 | ⇒ SI2392ADS-T1-E3 | D SI2392ADS-T1-GE3 | ⊛ SI2392ADS-T1-GE3 | ⊣ SI2392DS-T1-GE3 |
| ⊛ SI2392DS-T1-GE3 | D SI2399CDS-T1-GE3 | ⇒ SI2399DS-T1-GE3 | ↔ SI2399DS-T1-GE3 | ⇒ SI2400-BS |
| ⊣ SI2400-FS | ⊛ SI2400-FSR | ↔ SI2400-KS | ⇒ SI2400-KSR | ⇒ SI2401-FS |
| ⊛ SI2401-FSR | ⊣ SI2401-FSR. | ⊛ SI2401-KS | D SI2403-FTR | ⇒ SI2404-C-FSR |
| ↔ SI2404-C-FTR | ⊛ SI2404-C-ZSR | ⊣ SI2404-CFTRP | ⊛ SI2404-FS | ⇒ SI2404-FT |

Contact us: Info@Y-IC.com

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